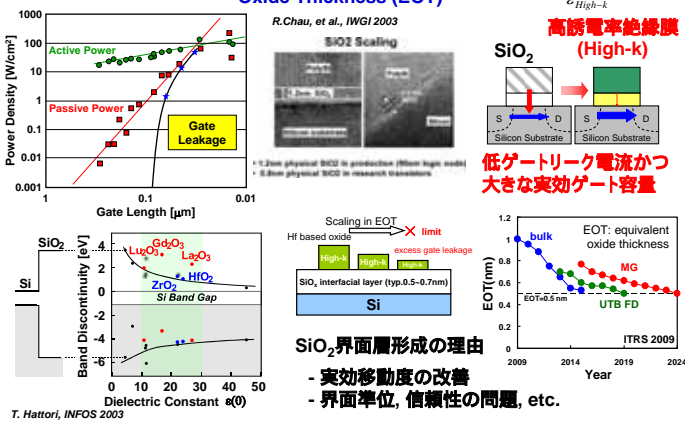




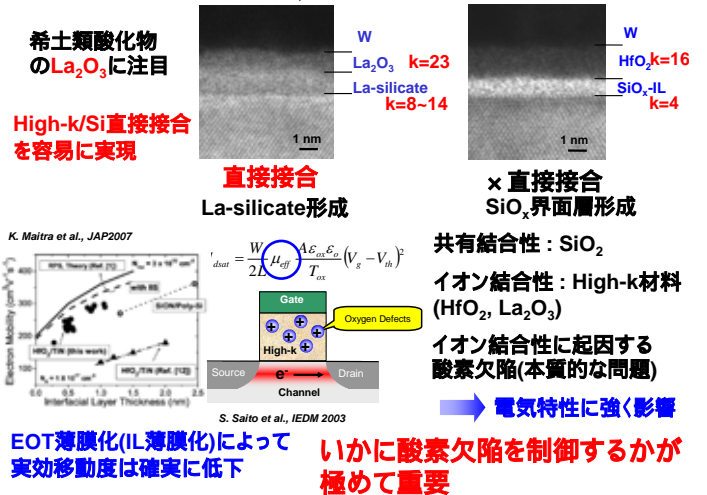
An Effective Process for Oxygen Defects Suppression for La-based Oxide Gate Dielectric

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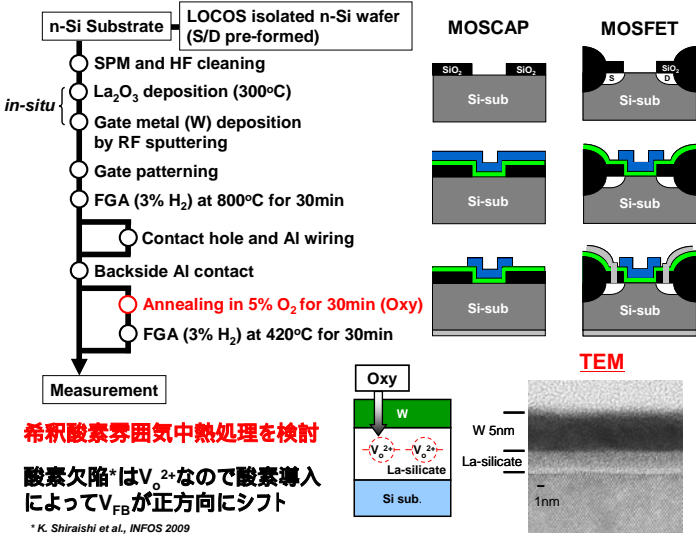
1. 背景



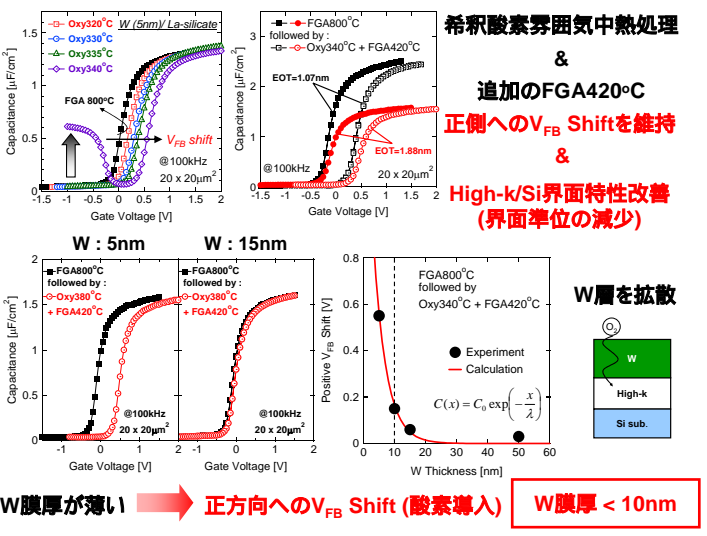
2. 目的



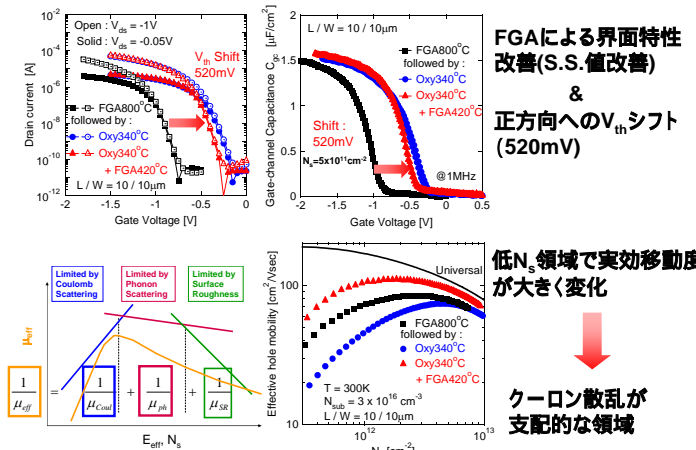
3. 実験方法



4-1. 実験結果 ~MOSCAP~



4-2 実験結果 ~pMOSFET~



5. まとめ

